

Amendments to the Specification

Please replace paragraph 0011 with the following amended paragraphs:

[0011] The metal CMP process may be used in a damascene sequence where micro-scratches or small trenches may be unintentionally formed across the metal pattern of an IC. By exposing the residue-filled micro-scratch to plasma suitable to remove the metal material, the residue will react with the plasma to create ~~an inert~~ a volatile gas that may results in the residue vacating the micro-scratch. The residue in the micro-scratch thereby may be reduced to an acceptable level, substantially eliminated or removed altogether.